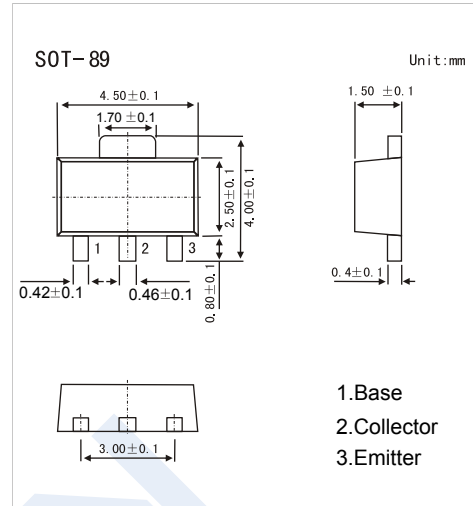


## PNP Transistors

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## ■ Features

- Low  $V_{CE(sat)}$

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	-40	V
Collector-Emitter Voltage	$V_{CEO}$	-32	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current (DC)	$I_c$	-1	A
Single pulse, $P_w=100\text{ms}$		-2	A
Collector Power Dissipation	$P_c$ *	0.5	W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature Range	$T_{stg}$	-55 to +150	$^\circ\text{C}$

\* When mounted on a 40x40x0.7mm ceramic board.

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

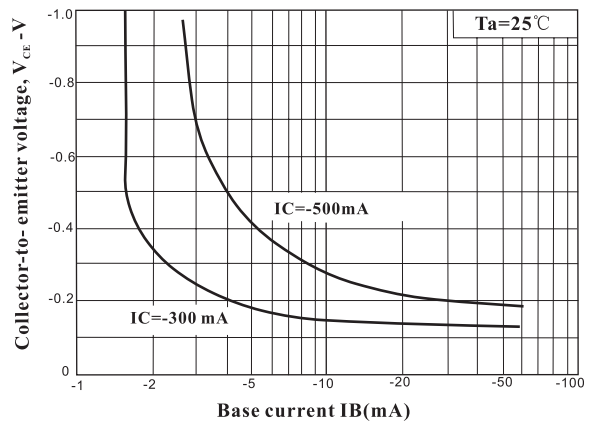
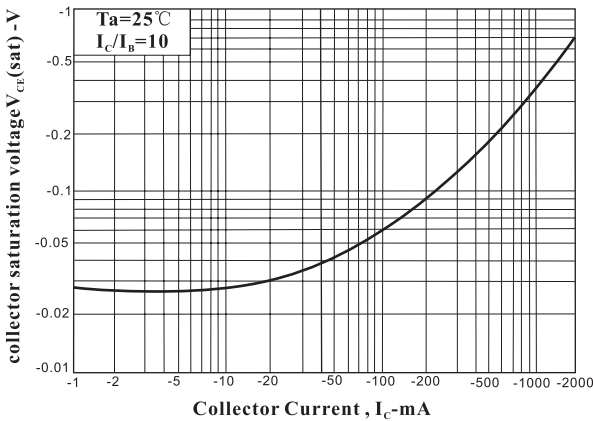
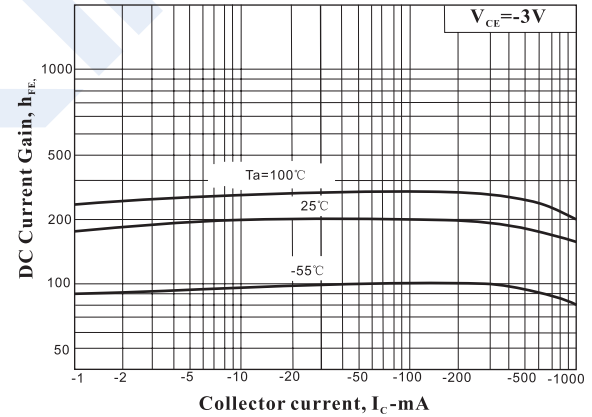
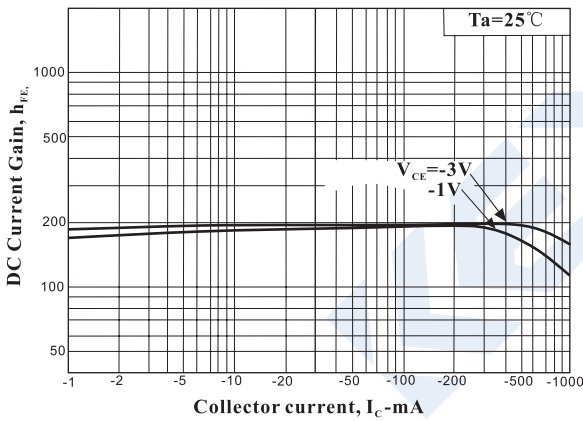
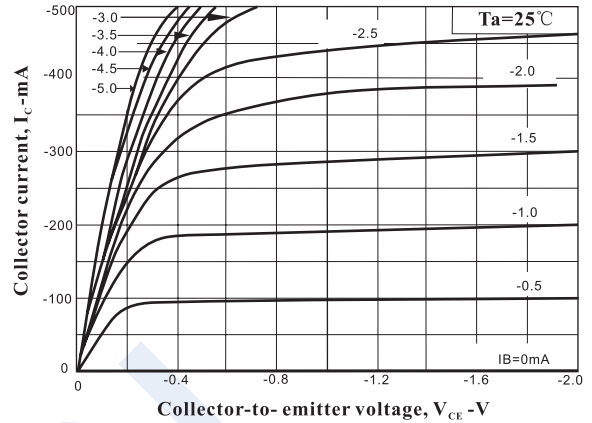
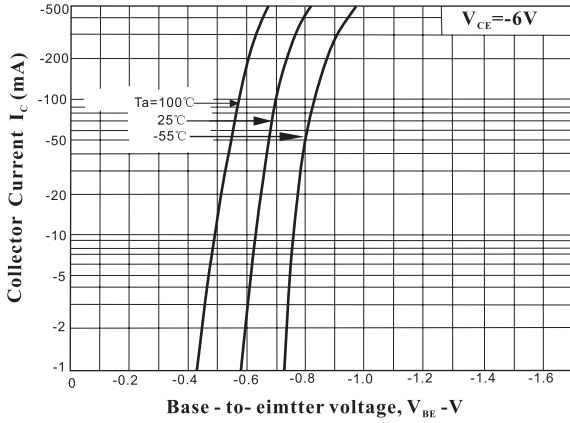
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CBO}$	$I_c = -50\mu\text{A}$ , $I_E = 0$	-40			V
Collector- emitter breakdown voltage	$V_{CEO}$	$I_c = -1\text{ mA}$ , $I_B = 0$	-32			
Emitter - base breakdown voltage	$V_{EBO}$	$I_E = -50\mu\text{A}$ , $I_C = 0$	-5			
Collector-base cut-off current	$I_{CBO}$	$V_{CB} = -20\text{ V}$ , $I_E = 0$			-0.5	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -4\text{ V}$ , $I_C = 0$			-0.5	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{ mA}$ , $I_B = -50\text{ mA}$		-0.2	-0.5	V
DC current gain	$h_{FE}$	$V_{CE} = -3\text{ V}$ , $I_c = -0.1\text{ A}$	82		390	
Collector output capacitance	$C_{ob}$	$V_{CB} = -10\text{ V}$ , $I_E = 0\text{ mA}$ , $f = 1\text{ MHz}$		20	30	$\text{pF}$
Transition frequency	$f_T$	$V_{CE} = -5\text{ V}$ , $I_E = 50\text{ mA}$ , $f = 30\text{ MHz}$		150		$\text{MHz}$

■  $h_{FE}$  Classification

Type	2KB4004-P	2KB4004-Q	2KB4004-R
Range	82-180	120-270	180-390
Marking	BAP*	BAQ*	BAR*

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■ Typical Characteristics



2?6 (\$\$)

■ Typical Characteristics

